



PJP8N60 / PJF8N60

600V N-Channel Enhancement Mode MOSFET

TO-220AB / ITO-220AB

FEATURES

- 8A , 600V, $R_{DS(ON)}=1.2\Omega@V_{GS}=10V, I_D=4.0A$
- Low ON Resistance
- Fast Switching
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- Specially Designed for AC Adapter, Battery Charge and SMPS
- In compliance with EU RoHs 2002/95/EC Directives

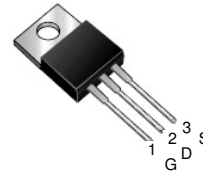
MECHANICAL DATA

- Case: TO-220AB / ITO-220AB Molded Plastic
- Terminals : Solderable per MIL-STD-750,Method 2026

ORDERING INFORMATION

| TYPE | MARKING | PACKAGE | PACKING |
|---------|---------|-----------|------------|
| PJP8N60 | P8N60 | TO-220AB | 50PCS/TUBE |
| PJF8N60 | F8N60 | ITO-220AB | 50PCS/TUBE |

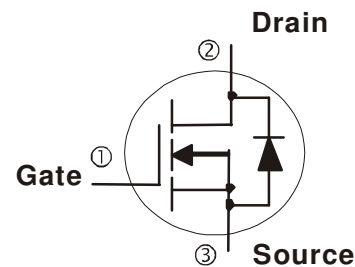
TO-220AB



ITO-220AB



INTERNAL SCHEMATIC DIAGRAM



Maximum RATINGS and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

| PARAMETER | Symbol | PJP8N60 | PJF8N60 | Units |
|---|-----------------|-------------|------------|--------------------|
| Drain-Source Voltage | V_{DS} | 600 | | V |
| Gate-Source Voltage | V_{GS} | ± 30 | | V |
| Continuous Drain Current | I_D | 8 | 8 | A |
| Pulsed Drain Current ¹⁾ | I_{DM} | 32 | 32 | A |
| Maximum Power Dissipation Derating Factor | P_D | 125 1.0 | 45 0.39 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | | $^\circ\text{C}$ |
| Avalanche Energy with Single Pulse $I_{AS}=8.0A, V_{DD}=50V, L=15.6mH$ | E_{AS} | 500 | | mJ |
| Junction-to-Case Thermal Resistance | $R_{\theta JC}$ | 1 | 2.78 | $^\circ\text{C/W}$ |
| Junction-to Ambient Thermal Resistance | $R_{\theta JA}$ | 62.5 | 100 | $^\circ\text{C/W}$ |

Note: 1. Maximum DC current limited by the package

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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Units |
|----------------------------------|---------------------|--|------|------|------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250uA | 600 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250uA | 2.0 | - | 4.0 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =10V, I _D =4.0A | - | 1.0 | 1.2 | Ω |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =600V, V _{GS} =0V | - | - | 10 | uA |
| Gate Body Leakage | I _{GSS} | V _{GS} =±30V, V _{DS} =0V | - | - | ±100 | nA |
| Dynamic | | | | | | |
| Total Gate Charge | Q _g | V _{DS} =480V, I _D =8A V _{GS} =10V | - | 22.8 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 5.6 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 7.6 | - | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} =300V, I _D =8A V _{GS} =10V, R _G =25Ω | - | 13.2 | 18 | ns |
| Turn-On Rise Time | t _r | | - | 18.4 | 32 | |
| Turn-Off Delay Time | t _{d(off)} | | - | 46.8 | 65 | |
| Turn-Off Fall Time | t _f | | - | 20.8 | 30 | |
| Input Capacitance | C _{iss} | V _{DS} =25V, V _{GS} =0V f=1.0MHz | - | 1165 | 1480 | pF |
| Output Capacitance | C _{oss} | | - | 108 | 160 | |
| Reverse Transfer Capacitance | C _{rss} | | - | 10 | 18 | |
| Source-Drain Diode | | | | | | |
| Max. Diode Forward Current | I _S | - | - | - | 8.0 | A |
| Max.Pulsed Source Current | I _{SM} | - | - | - | 32 | A |
| Diode Forward Voltage | V _{SD} | I _S =8A, V _{GS} =0V | - | - | 1.4 | V |
| Reverse Recovery Time | t _{rr} | V _{GS} =0V, I _F =8A di/dt=100A/us | - | 350 | - | ns |
| Reverse Recovery Charge | Q _{rr} | | - | 3.2 | - | uC |

NOTE: Plus Test : Pluse Width ≤ 300us, Duty Cycle ≤ 2%.



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Typical Characteristics Curves ($T_a=25^\circ\text{C}$, unless otherwise noted)

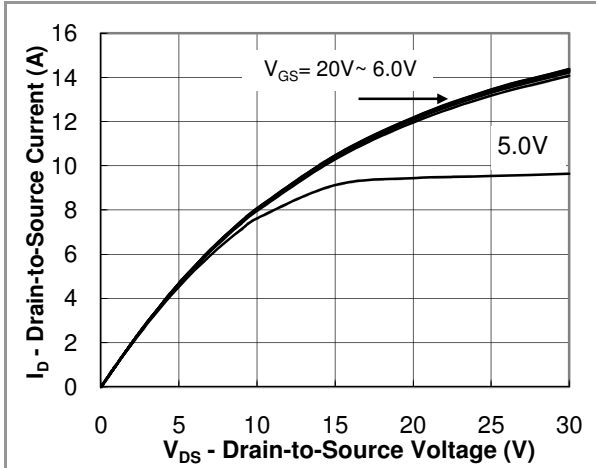


Fig.1 Output Characteristic

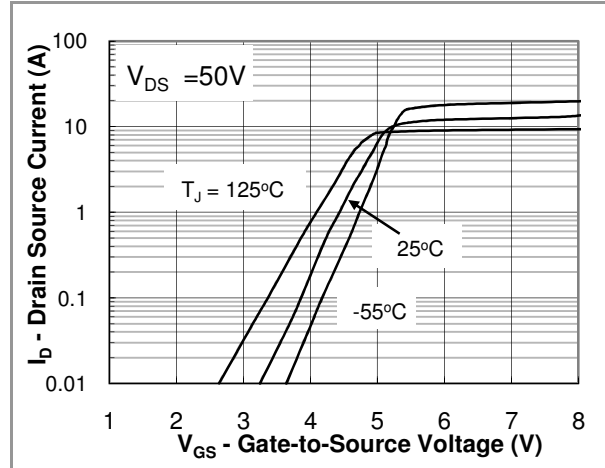


Fig.2 Transfer Characteristic

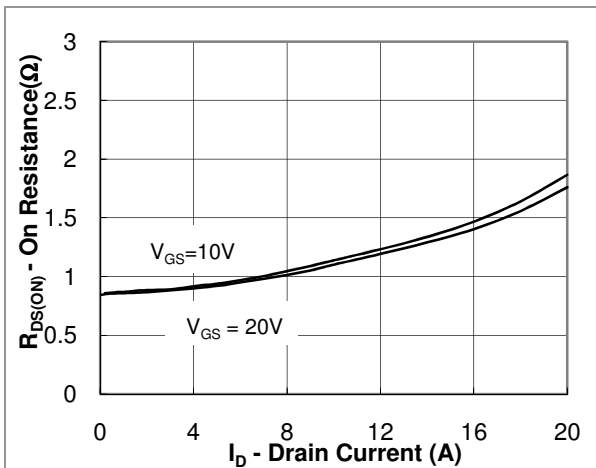


Fig.3 On Resistance vs Drain Current

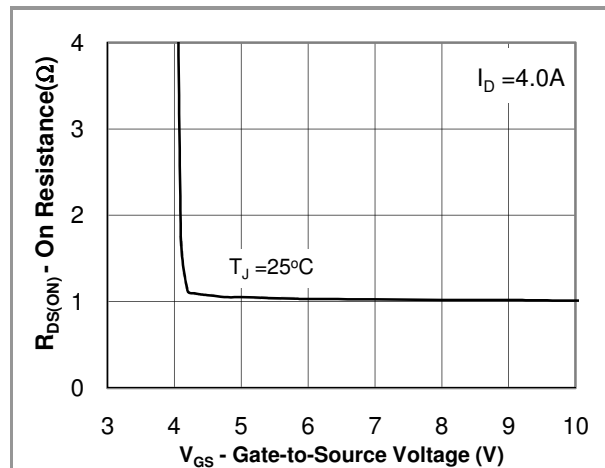


Fig.4 On Resistance vs Gate to Source Voltage

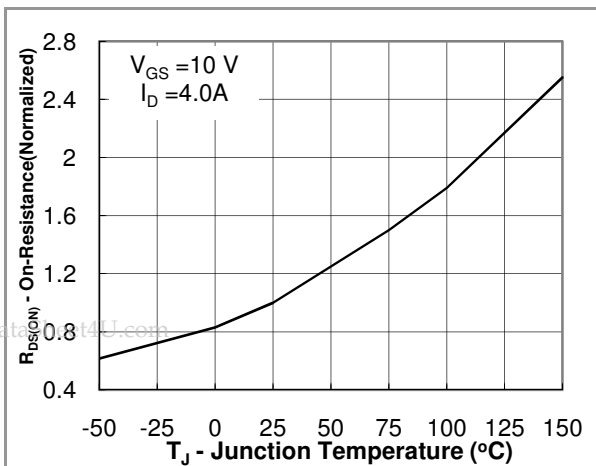


Fig.5 On Resistance vs Junction Temperature

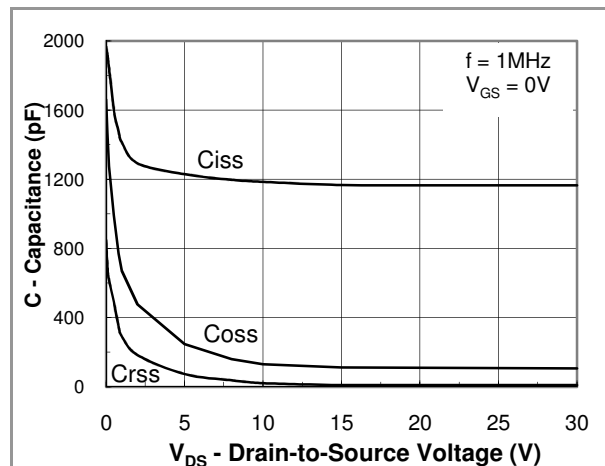


Fig.6 Capacitance



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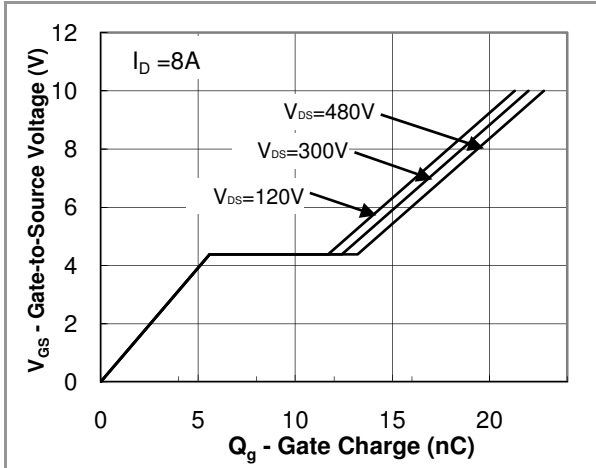


Fig. 7 Gate Charge Waveform

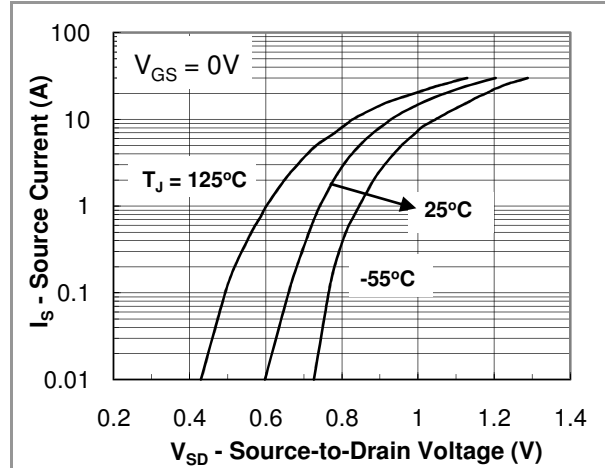


Fig.8 Source-Drain Diode Forward Voltage

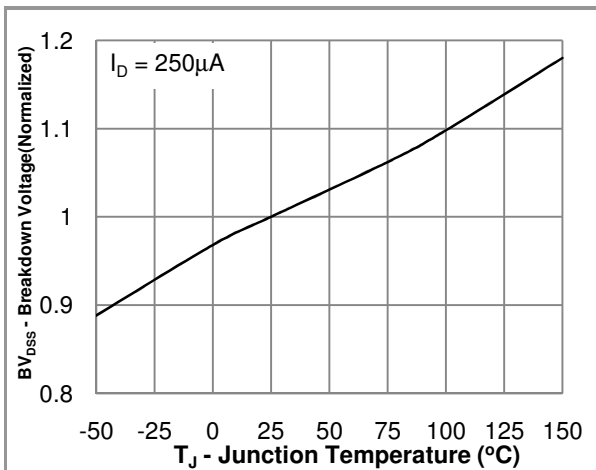


Fig.9 Breakdown Voltage vs Junction Temperature



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